

A. BOOK ARTICLES

3. K. Tillmann, H. Trinkaus, W. Jäger: *Self-assembled SiGe nanostructures*. In: Silicon Germanium and SiGe: Carbon (Eds. E. Kasper, K. Lyutovich, INSPEC Institution of Electrical Engineers, London), EMIS Data Review Series No. 24, 63 - 74 (2000)
2. W. Jäger: *Ordering in SiGe alloys*. In: Silicon Germanium and SiGe: Carbon (Eds. E. Kasper, K. Lyutovich, INSPEC Institution of Electrical Engineers, London), EMIS Data Review Series No. 24, 50 - 58 (2000)
1. W. Jäger: *Ordering in Si_{1-x}Ge_x Alloys*. In: Properties of Strained and Relaxed Silicon Germanium (Ed. E. Kasper, INSPEC Institution of Electrical Engineers London) EMIS Data Review Series No. 12, 53 - 60 (1995)

B. PUBLICATIONS IN JOURNALS

126. E. Spiecker, M. Garbrecht, W. Jäger, K. Tillmann, *Advantages of aberration correction for HRTEM investigation of complex layer compounds*, Journal of Microscopy, Vol. 237, 3, 341 – 346, 2010.
125. D. Häußler, C. Morawe, U. Roß, B. Ögüt, E. Spiecker, W. Jäger, F. Hertlein, U. Heidorn, J. Wiesmann, *Aperiodic W/B₄C multilayer systems for X-ray optics: Quantitative determination of layer thickness by HAADF-STEM and X-ray reflectivity*, Surface and Coatings Technology, SCT-15339, 2009.
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118. J. Schöne, E. Spiecker, W. Jäger, F. Dimroth, A.W. Bett, *Comparative TEM and HRXRD analyses of strain relaxation in step-graded GaInAs buffer-layers for high-efficiency solar cells*, Microsc. Microanal., 12 (Supp. 2), 918 (2006).

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115. M. Behrens, R. Kiebach, W. Bensch, D. Häußler, W. Jäger, *Synthesis of thin Cr₃Se₄-films from modulated elemental reactants via two amorphous intermediates: A detailed examination of the reaction mechanism*, *Inorg. Chem.*, 45, 2704-2712 (2006).
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